



# **isc** Silicon PNP Power Transistor

#### **DESCRIPTION**

- · Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub>= -80(V)(Min.)
- · Low Collector Saturation Voltage
  - $V_{CE(sat)} = -0.3(V)(Max.)@I_{C} = -5A$
- Large Current Capability-I<sub>C</sub>= -10A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## **APPLICATIONS**



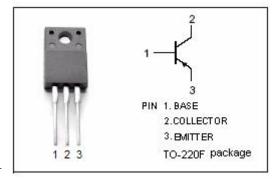
 Designed for use as a driver in DC/DC converters and actuators.

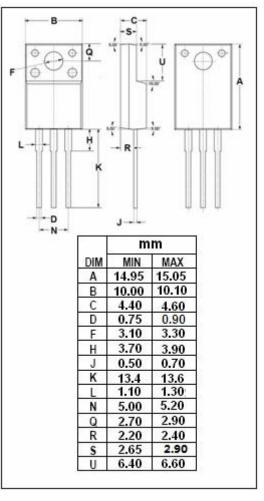
## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	-80	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-80	V
V <sub>EBO</sub>	Emitter-Base Voltage	-7	V
Ic	Collector Current-Continuous	А	
I <sub>CM</sub>	Collector Current-Peak	-20	А
I <sub>B</sub>	Base Current-Continuous	-1.5	А
I <sub>BM</sub>	Base Current-Peak	-2	Α
Pc	Total Power Dissipation @ T <sub>C</sub> =25°C  25		W
TJ	Junction Temperature 150		$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range -55~150		${\mathbb C}$

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	5	°C/W







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2SA1880

### **ELECTRICAL CHARACTERISTICS**

T<sub>c</sub>=25℃ unless otherwise specified

10-23 C ui	1c-25 C unless otherwise specified								
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	Ic= -0.1A; I <sub>B</sub> = 0	-80			V			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -5A; I <sub>B</sub> = -0.5A			-0.3	V			
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -5A; I <sub>B</sub> = -0.5A			-1.2	V			
Ісво	Collector Cutoff Current	V <sub>CB</sub> = -80V; I <sub>E</sub> = 0			-100	μА			
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = -80V; I <sub>B</sub> = 0			-100	μА			
І <sub>ЕВО</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -7V; I <sub>C</sub> = 0			-100	μА			
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = -5A; V <sub>CE</sub> = -2V	70						
f⊤	Current-Gain—Bandwidth Product	Ic= -1A; V <sub>CE</sub> = -10V		50		MHz			
Switching Times									
ton	Turn-on Time				0.3	μs			
t <sub>stg</sub>	Storage Time	$I_{C}$ = -5A, $I_{B1}$ = - $I_{B2}$ = -0.5A, $R_{L}$ = 5 $\Omega$ , $V_{BB2}$ = -4V;			1.5	μS			
t <sub>f</sub>	Fall Time				0.2	μ <b>s</b>			

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